Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1-17. Canceled.

18. (Original) A method for forming a semiconductor device, the method comprising:

a) providing a semiconductor substrate having a first region of a first conductivity type;

b) forming a region of a second conductivity type in the semiconductor substrate;

c) forming a first charge control electrode; and

d) forming a second charge control electrode, wherein the first charge control electrode is adapted to be biased differently than the first charge control electrode.

19. (Original) The method of claim 18 further comprising forming a trench in the semiconductor substrate and wherein forming the first charge control electrode comprises depositing a conductive material in the trench and then etching the deposited conductive material.

20. (Original) The method of claim 19 wherein the conductive material is a first conductive material and wherein forming the second charge control electrode comprises depositing a second conductive material in the trench and then etching the deposited second conductive material.

21. (Original) The method of claim 18 further comprising:
forming a trenched gate structure in the semiconductor substrate.

22. (Original) The method of claim 18 wherein the first and second charge control electrodes comprise polysilicon.

23. (Original) The method of claim 18 wherein the method further comprises forming a plurality of biasing elements on or in the semiconductor substrate, wherein the biasing elements are adapted to bias the first and second charge control electrodes at different voltages.

24. (Original) The method of claim 18 wherein the semiconductor device is a power MOSFET.

25-29. Canceled.

30. (Original) A method for forming a field effect transistor comprising:

a) providing a semiconductor substrate of a first conductivity type having a major surface, a drift region, and a drain region;

b) forming a well region of a second conductivity type in the semiconductor substrate;

c) forming a source region of the first conductivity type in the well region;

d) forming a source contact layer on the source region;

e) forming a gate electrode adjacent to the source region;

f) forming a charge control electrode in the drift region, wherein the charge control electrode is adapted to be biased at a different potential than the gate electrode or the source contact layer, and is adapted to control the electric field in the drift region; and

g) forming a dielectric material around the charge control electrode.

31. (Original) The method of claim 30 wherein the gate electrode is a trenched gate electrode.

32. (Original) The method of claim 30 further comprising:

forming a biasing element, wherein the biasing element is adapted to bias the charge control electrode.